	! " #	$! % & '	! ( ) % * +	, -	. /
			0 1 2 3 4 5 6 7 8	9 :	; < =
			> ? @ A B C D B C D E F G H I J K L H	M N O	P Q R
			$R_{DS(on)}$ V_{GS}=10V I_D=50A 最大值 5.5 mΩ 改为 3.8 mΩ;波峰焊改为回流焊	9 :	M N O
			S T U	9 :	M N O

V W X Y Z > [U

BRCS100N03BD

Rev.B May.-2022

DATA SHEET

/ Descriptions

TO-263 \ Y Y Z N] ^ MOS _ ` a b c

N-CHANNEL MOSFET in a TO-263 Plastic Package.

/ Features

d e f g d h i f + j K k l m n 5 6 o p c

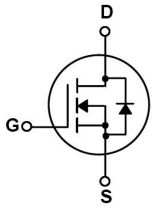
Low gate charge, low crss, fast switching,

/ Applications

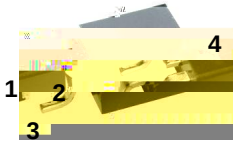
q r s t u v w x t u j K c

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 y G PIN 2 y D PIN 3 y S PIN 4 y D

/ Marking

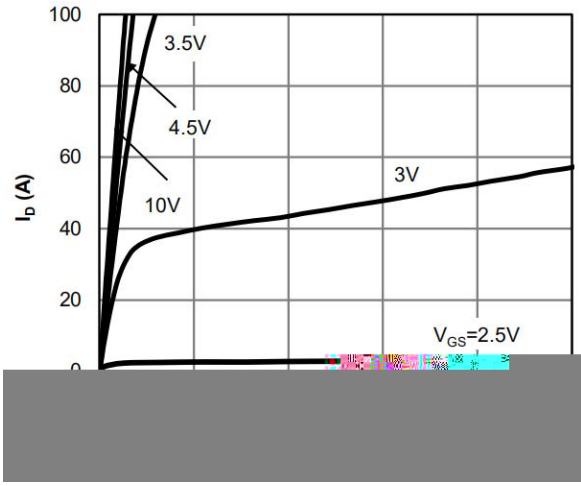
z { | } ~ c See Marking Instructions.

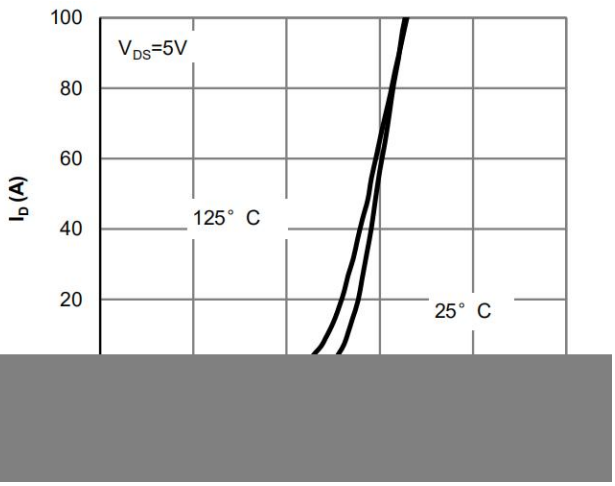
	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	30	V

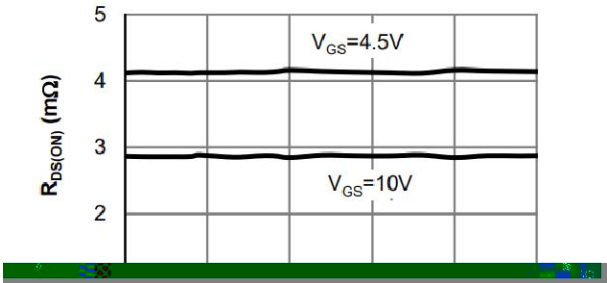
/ Electrical Characteristics(Ta=25)

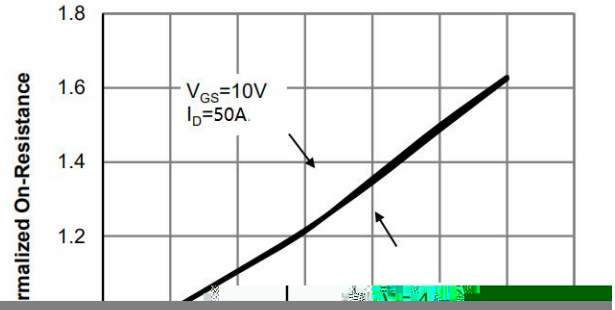
参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V, V_{DS}=15V, I_D=20A		80		nC
Total Gate Charge	$Q_{g(4.5V)}$			35		
Gate Source Charge	Q_{gs}			13		
Gate Drain Charge	Q_{gd}			13		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=15V I_D=1A R_{GEN}=6Ω V_{GS}=10V		25.7	50	ns
Turn-On Rise Time	t_r			10	20	ns
Turn-Off Delay Time	$t_{d(off)}$			128	200	ns
Turn-Off Fall Time	t_f			34	70	ns

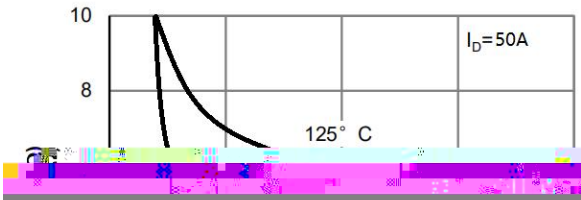
/ Electrical Characteristic Curve

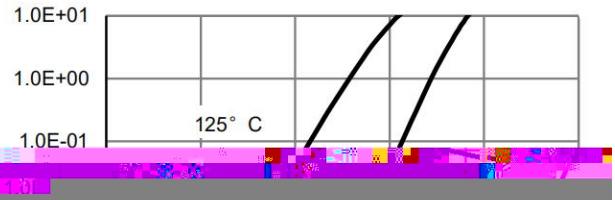




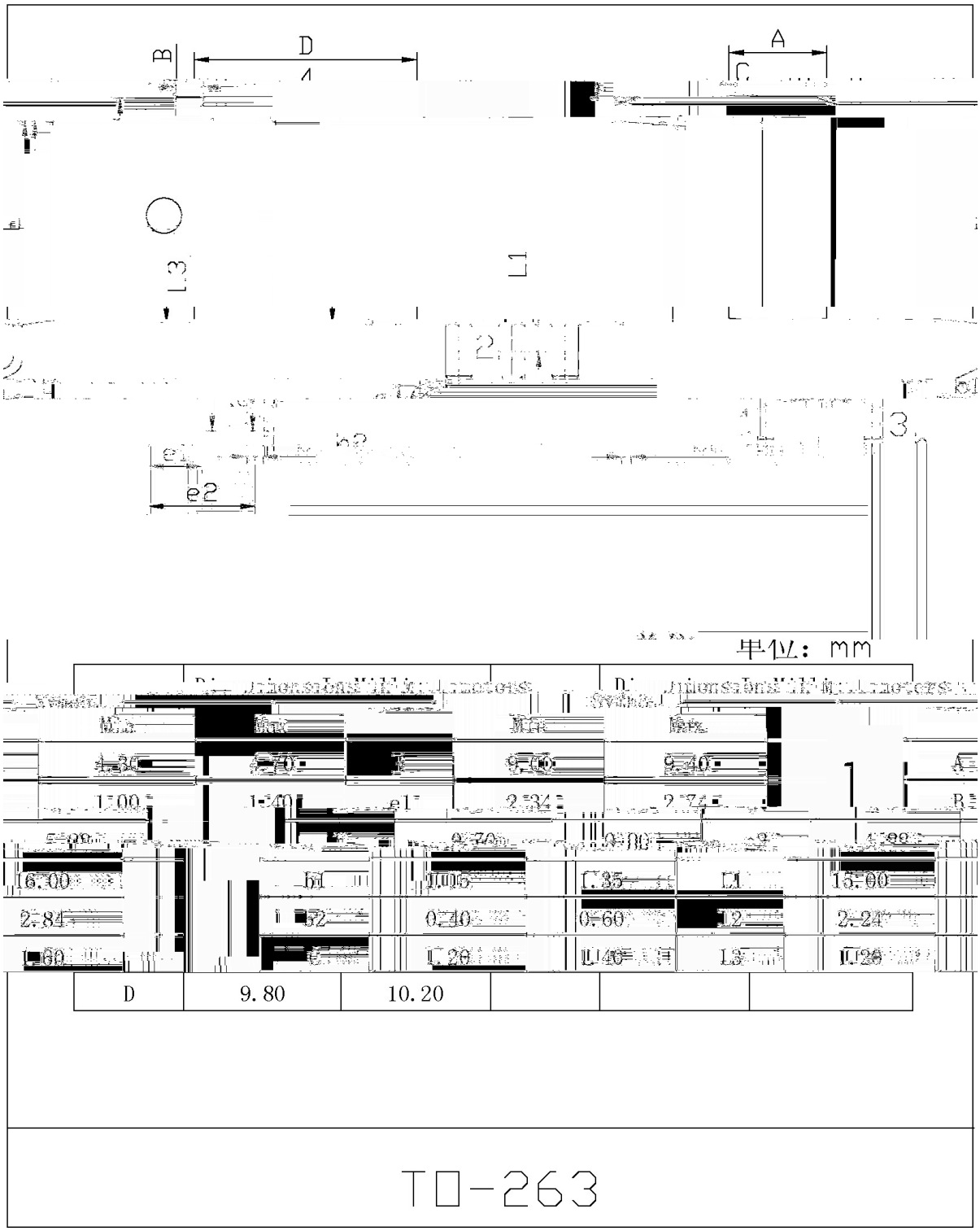




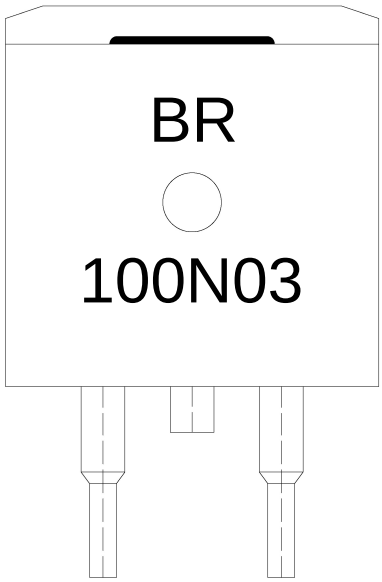




/ Package Dimensions



/ Marking Instructions



BR

100N03

****

Note:

BR:	Company Code
100N03:	Product Type
****:	Lot No. Code, code change with Lot No

( ) /

Note:

1 150 180 60 90sec;
1.Preheating:150~180℃, Time:60~90sec.

2 245±5 5±0.5sec;
2.Peak Temp.:245±5℃, Duration:5±0.5sec.

3 2 10℃/sec.
3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃ 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL